	Application No.	Applicant(s)  TODD ET AL.	
Notice of Allowability	10/074,564		
	Examiner	Art Unit	
	Brook Kebede	2823	
The MAILING DATE of this communication apperature.  All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313  1. This communication is responsive to 21 April 2005.  2. The allowed claim(s) is/are 1.6-26.55-68 and 72-75.  3. The drawings filed on 11 February 2002 are accepted by the drawings filed on 11 February 2002 are accepted by the Discount of the communication is made of a claim for foreign priority under the communication appears to the priority documents have	ears on the cover sheet we (OR REMAINS) CLOSED or other appropriate comming IGHTS. This application is a and MPEP 1308.  The Examiner.  The examiner of the cover sheet we have a second sheet with the cover sheet with th	ith the correspondence add in this application. If not include nunication will be mailed in due subject to withdrawal from issert of or (f).	ded e course. <b>THIS</b>
<ol><li>Certified copies of the priority documents have</li></ol>	e been received in Applicati	ion No	
3. Copies of the certified copies of the priority do International Bureau (PCT Rule 17.2(a)).  * Certified copies not received:  Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	of this communication to fil	- 1	
<ol> <li>A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give</li> </ol>	itted. Note the attached EXes reason(s) why the oath o	AMINER'S AMENDMENT or I	NOTICE OF
<ul> <li>6. ☐ CORRECTED DRAWINGS ( as "replacement sheets") must</li> <li>(a) ☐ including changes required by the Notice of Draftspers</li> <li>1) ☐ hereto or 2) ☐ to Paper No./Mail Date</li> <li>(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date</li> <li>Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t</li> <li>7. ☐ DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT</li> </ul>	son's Patent Drawing Revie  s Amendment / Comment of  .84(c)) should be written on the header according to 37 C sit of BIOLOGICAL MAT	or in the Office action of the drawings in the front (not th FR 1.121(d). ERIAL must be submitted.	
Attachment(s)  1. ☐ Notice of References Cited (PTO-892)  2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)  3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 8/22/03;1/31/05  4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ⊠ Interview S Paper No 8), 7. ⊠ Examiner's		lowance
		BOOK KEBEDE PATENT EXAMINI	

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### **DETAILED ACTION**

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# Information Disclosure Statement

1. The information disclosure statement (IDS) submitted on August 22, 2003 was filed before the mailing date of the Final Office action of January 25, 2005. The submission is in compliance with the provisions of 37 CFR 1.97. Accordingly, the information disclosure statement is being considered by the examiner and a copy of PTO-1449 is attached hereto.

2. The information disclosure statement filed on January 31, 2005 (or certificate mailing date of January 26, 2005) fails to comply with 37 CFR 1.97(d) because it lacks the fee set forth in 37 CFR 1.17(p). It has been placed in the application file, but the information referred to therein has not been considered.

#### **EXAMINER'S AMENDMENT**

3. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Mr. Joseph J. Mallon on April 28, 2004.

4. The application has been amended as follows:

## In the claims:

In claim 1, lines 6-7, change "the Si-containing" to --the <u>amorphous</u> Si-containing--. In claim 6, line 1, change "the Si-containing" to --the <u>amorphous</u> Si-containing--. In claim 9, line 2, change "the Si-containing" to --the <u>amorphous</u> Si-containing--.

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In claim 10, line 1, change "the Si-containing" to --the amorphous Si-containing--. In claim 11, line 2, change "the Si-containing" to --the amorphous Si-containing--. In claim 14, line 1, change "the Si-containing" to --the amorphous Si-containing--. In claim 18, line 1, change "the Si-containing" to --the amorphous Si-containing--. In claim 19, line 1, change "the Si-containing" to --the amorphous Si-containing--. In claim 19, lines 2-3, change "the Si-containing" to --the amorphous Si-containing--. In claim 22, line 1, change "the Si-containing" to --the amorphous Si-containing--. In claim 25, line 1, change "the Si-containing" to --the amorphous Si-containing--. In claim 55, line 5, change "the Si-containing" to --the amorphous Si-containing--. In claim 55, line 9, change "the Si-containing" to --the amorphous Si-containing--. In claim 55, line 10, change "the Si-containing" to --the amorphous Si-containing--. In claim 59, line 5, change "the Si-containing" to --the amorphous Si-containing--. In claim 59, line 9, change "the Si-containing" to --the amorphous Si-containing--. In claim 60, line 5, change "the Si-containing" to --the amorphous Si-containing--. In claim 62, line 5, change "the Si-containing" to --the amorphous Si-containing--. In claim 63, line 1, change "the Si-containing" to --the amorphous Si-containing--. In claim 64, lines 1-2, change "the Si-containing" to --the amorphous Si-containing--. In claim 64, line 3, change "the Si-containing" to --the amorphous Si-containing--. In claim 72, line 6, change "the Si-containing" to --the amorphous Si-containing--. In claim 72, line 7, change "the Si-containing" to --the amorphous Si-containing--. In claim 73, line 6, change "the Si-containing" to -- the amorphous Si-containing--.

# Allowable Subject Matter

5. Claims 1, 6-26, 55-68 and 72-75 are allowed over prior art of record.

# Reasons for Allowance

6. The following is an examiner's statement of reasons for allowance:

The instant application claimed invention is allowed in view of the Terminal Disclaimer that was filed on March 22, 2005. In addition, the prior art of record neither anticipates nor renders obvious the claimed subject matter of the instant application as a whole either taken alone or in combination, in particular, prior art of record does not teach "depositing an amorphous Si-containing film onto the substrate, the amorphous Si-containing film having a thickness in the range of 10 Å to 150 Å and a film surface roughness that is greater than the substrate surface roughness by an amount of about 5 Å rms or less, over a surface area of about one square micron or greater," as recited in claims 1, 59, 60 and 62 respectively, "depositing an amorphous Si-containing film onto the substrate, the amorphous Si-containing film having a thickness in the range of 10 Å to 150 Å and a film surface roughness that is greater than the substrate surface roughness by an amount of about 5 Å rms or less, over a surface area of about one square micron or greater; depositing an oxide layer directly onto the amorphous Sicontaining film; and annealing the amorphous Si-containing film to form a plurality of quantum dots," as recited in claim 55, "depositing a Si-containing film onto the substrate, the Sicontaining film having a thickness in the range of 10 Å to 150 Å and a film surface roughness that is greater than the substrate surface roughness by an amount of about 5 Å rms or less, over a surface area of about one square micron or greater; and depositing a doped Si-containing layer directly onto the Si-containing film; wherein the Si-containing film is deposited directly onto a

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dielectric material," as recited in claim 56, "depositing a Si-N film onto the substrate, the Si-N film having a thickness in the range of 10 Å to 150 Å and a film surface roughness that is greater than the substrate surface roughness by an amount of about 5 Å rms or less, over a surface area of about one square micron or greater," as recited in claim 65, "depositing a continuous amorphous Si-containing film having a thickness of less than about 100 Å and a surface area of about one square micron or larger onto the substrate by thermal chemical vapor deposition; depositing an oxide layer over the amorphous Si-containing film; and annealing the amorphous Si-containing film to form a plurality of quantum dots," as recited in claim 72, and "depositing a continuous amorphous Si-containing film having a thickness of less than about 100 Å and a surface area of about one square micron or larger onto the substrate by thermal chemical vapor deposition; and depositing a doped Si-containing layer directly onto the amorphous Si-containing film," as recited in claim 73.

Claims 6-26, 57, 58, 61, 63, 64, 66-68, 74, and 75 are also allowed as being directly or indirectly dependent of the allowed independent base claim.

# Conclusion

7. Any comments considered necessary by applicants must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Correspondence

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8. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Brook Kebede whose telephone number is (571) 272-1862. The

examiner can normally be reached on 8-5 Monday to Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Olik Chaudhuri can be reached on (571) 272-1855. The fax phone number for the

organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Brook Kebede

Broon Keheele

Patent Examiner

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BK

April 28, 2005